P & N-Channel 30-V (D-S) MOSFET

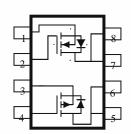
These miniature surface mount MOSFETs utilize High Cell Density process. Low $r_{DS(on)}$ assures minimal power loss and conserves energy, making this device ideal for use in power management circuitry. Typical applications are PWMDC-DC converters, power management in portable and battery-powered products such as computers, printers, battery charger, telecommunication power system, and telephones power system.

$V_{DS}(V)$	$r_{DS(on)}m(\Omega)$	$I_{D}(A)$
30	$28 @ V_{GS} = 4.5V$	7.2
	$18 @ V_{GS} = 10V$	8.5
-20	$250 @ V_{GS} = -2.5V$	-2.6
	$170 @ V_{GS} = -4.5V$	-3.2

- Low r_{DS(on)} Provides Higher Efficiency and Extends Battery Life
- Miniature SO-8 Surface Mount Package Saves Board Space
- High power and current handling capability
- Low side high current DC-DC Converter applications



PRODUCT SUMMARY



ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)							
Parameter			N-Channel	P-Channel	Units		
Drain-Source Voltage		V_{DS}	30	-20	V		
Gate-Source Voltage			20	-12	٧		
	$T_A=25^{\circ}C$	T	10	-3.5			
Continuous Drain Current ^a	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	¹ D	7	-2.3	A		
Pulsed Drain Current ^b			±50	±50			
Continuous Source Current (Diode Conduction) ^a			2.3	-2.1	A		
D	$T_A=25^{\circ}C$	D	2.1	2.1	W		
Power Dissipation ^a	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	¹ D	1.3	1.3	VV		
Operating Junction and Storage Temperature Range				-55 to 150	°C		

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Maximum	Units				
Maximum Junction-to-Case ^a	t <= 5 sec	$R_{ heta JC}$	40	°C/W			
Maximum Junction-to-Ambient ^a	t <= 5 sec	$R_{\theta JA}$	60	°C/W			

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature



· · · · · · · · · · · · · · · · · · ·		Test Conditions	Limits				
Parame te r	Symbol		Ch		Typ	Max	Unit
Static			· •			•	
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS},I_D=250~uA$	N	1			V
Gate-Timeshold Voltage	▼ GS(th)	$V_{GS} = V_{DS}$, $I_D = -250 \text{ uA}$	P	-0.7			
Gate-Body Leakage	I_{GSS}	VGS = -12 V, VDS = 0 V	P			±100	nA
, ,	GBS	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$ $V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$	N P	1		±100	117.1
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$	N	1		-1 1	uA
0 g A	т т	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	N	30		1	
On-State Drain Current ^A	$I_{D(on)}$	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	P	-10		1	Α
		$VGS = 10 \text{ V}, I_D = 8.5 \text{ A}$	N			18	
Drain-Source On-Resistance ^A	$r_{DS(on)}$	$VGS = 4.5 \text{ V}, I_D = 7.2 \text{ A}$	1,			28	mΩ
		VGS = -4.5 V, I _D = -3.2 A VGS = -2.5 V, I _D = -2.6 A	P	1		170 250	
	+	$V_{DS} = 15 \text{ V}, I_D = 10 \text{ A}$	N	1	40	230	
Forward Tranconductance ^A	g_{fs}	$V_{DS} = -15 \text{ V}, I_{D} = -9.5 \text{ A}$	P		31		S
Dynamic			<u>.</u>			•	
Total Gate Charge	0	N-Channel V _{DS} =15V,	N		20		
Total Gate Charge	Qg		P		4]
Gate-Source Charge	Q_{gs}	$V_{GS}=10V$, $I_{D}=10A$ P-	N P		7 0.8		nC
		Channel	N	1	7	1	
Gate-Drain Charge	Q_{gd}	V_{DS} =-15V, V_{GS} =-10V, I_{D} =-5A	P		1		
			N	<u> </u>	20		
Turn-On Delay Time	$t_{d(on)}$	N-Chaneel	P		5	1	
		$V_{DD} = 15V$, $V_{GS} = 10V$, $I_{D} = 1A$,	N		9		
Rise Time	$t_{ m r}$	t_r $R_{GEN}=25\Omega$, P	4				
Turn Off Dalay Time	t., a	P-Channel	N		70		nS
Turn-Off Delay Time	t _{d(off)}	V_{DD} =-15V, V_{GS} =-10V, I_{D} =-1A	P		31		
Fall-Time	t_{f}	$R_{GEN}=15\Omega$	N		20		
1 dii-1 liik	CI.		P		28		

Notes

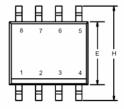
- a. Pulse test: $PW \le 300us duty cycle \le 2\%$.
- b. Guaranteed by design, not subject to production testing.

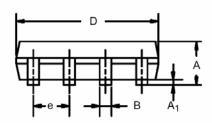
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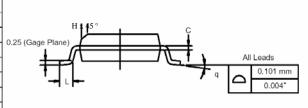
Package Information

SO-8: 8LEAD





	MILLIN	IETERS	INC	HES
Dim	Min	Max	Min	Max
Α	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
В	0.35	0.51	0.014	0.020
С	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
е	1.27 BSC		0.050	BSC
Н	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°



Ordering information

AM4528C-T1-XX

A: Analog Power

- M: MOSFET

– 4528: Part number

- C: Complementary

- T1: Tape & reel

- XX: Blank: Standard

PF: Leadfree